HALOGEN FREE



## Vishay Semiconductors

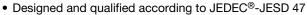
# Ultrafast Rectifier, 8 A FRED Pt®



| PRIMARY CHARACTERISTICS          |                    |  |  |  |  |  |  |  |
|----------------------------------|--------------------|--|--|--|--|--|--|--|
| I <sub>F(AV)</sub>               | 8 A                |  |  |  |  |  |  |  |
| $V_{R}$                          | 200 V              |  |  |  |  |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.895 V            |  |  |  |  |  |  |  |
| t <sub>rr</sub> typ.             | See Recovery table |  |  |  |  |  |  |  |
| T <sub>J</sub> max.              | 175 °C             |  |  |  |  |  |  |  |
| Package                          | TO-220AC 2L        |  |  |  |  |  |  |  |
| Circuit configuration            | Single             |  |  |  |  |  |  |  |

#### **FEATURES**

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

VS-MUR820 is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS                    |                    |   |             |       |  |  |  |  |  |
|---|--------------------|---|-------------|-------|--|--|--|--|--|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS   | MAX.        | UNITS |  |  |  |  |  |
| Peak repetitive reverse voltage             | $V_{RRM}$          |   | 200         | V     |  |  |  |  |  |
| Average rectified forward current           | I <sub>F(AV)</sub> | Total device, rated V <sub>R</sub> , T <sub>C</sub> = 150 °C        | 8           |       |  |  |  |  |  |
| Non-repetitive peak surge current           | I <sub>FSM</sub>   |   | 100         | Α     |  |  |  |  |  |
| Peak repetitive forward current             | I <sub>FM</sub>    | Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 150 °C | 16          |       |  |  |  |  |  |
| Operating junction and storage temperatures | $T_J$ , $T_{Stg}$  |   | -65 to +175 | °C    |  |  |  |  |  |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                                     |   |      |      |       |       |  |  |  |  |
|--|-------------------------------------|---|------|------|-------|-------|--|--|--|--|
| PARAMETER  | SYMBOL                              | TEST CONDITIONS   | MIN. | TYP. | MAX.  | UNITS |  |  |  |  |
| Breakdown voltage,<br>blocking voltage   | V <sub>BR</sub> ,<br>V <sub>R</sub> | Ι <sub>R</sub> = 100 μΑ                                 | 200  | -    | -     | .,    |  |  |  |  |
| Campand caltage  | V <sub>F</sub>                      | I <sub>F</sub> = 8 A                                    | -    | -    | 0.975 | V     |  |  |  |  |
| Forward voltage  |                                     | I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C           | -    | -    | 0.895 |       |  |  |  |  |
| Reverse leakage current  | ront                                | $V_R = V_R$ rated                                       | -    | -    | 5     |       |  |  |  |  |
| neverse leakage current  | I <sub>R</sub>                      | $T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$ | -    | -    | 250   | μΑ    |  |  |  |  |
| Junction capacitance   | C <sub>T</sub>                      | $V_{R} = 200 \text{ V}$                                 | -    | 25   | -     | pF    |  |  |  |  |
| Series inductance L <sub>S</sub>   |                                     | Measured lead to lead 5 mm from package body            | -    | 8.0  | -     | nH    |  |  |  |  |



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| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                  |                          |  |      |      |      |       |  |  |
|---|------------------|--------------------------|--|------|------|------|-------|--|--|
| PARAMETER   | SYMBOL           | TEST CO                  | NDITIONS   | MIN. | TYP. | MAX. | UNITS |  |  |
|   |                  | $I_F = 1.0 A, dI_F/dt =$ | 50 A/μs, V <sub>R</sub> = 30 V                         | -    | -    | 35   |       |  |  |
| Poverse receivery time  | t <sub>rr</sub>  | $I_F = 0.5 A, I_R = 1.0$ | ı  | ı    | 25   |      |       |  |  |
| Reverse recovery time   |                  | T <sub>J</sub> = 25 °C   |  | -    | 20   | -    | ns    |  |  |
|   |                  | T <sub>J</sub> = 125 °C  |  | -    | 34   | -    |       |  |  |
| Dook room ourrent   | I <sub>RRM</sub> | T <sub>J</sub> = 25 °C   | I <sub>F</sub> = 8 A<br>dI <sub>F</sub> /dt = 200 A/µs | -    | 1.7  | -    | Α     |  |  |
| Peak recovery current   |                  | T <sub>J</sub> = 125 °C  | V <sub>R</sub> = 160 V                                 | -    | 4.2  | -    | A     |  |  |
| Povorno rocovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 25 °C   |  | ı    | 23   | -    | nC    |  |  |
| Reverse recovery charge   |                  | T <sub>J</sub> = 125 °C  |  | -    | 75   | -    |       |  |  |

| THERMAL - MECHANICAL SPECIFICATIONS            |                                   |   |              |      |            |                        |  |  |  |  |
|--|-----------------------------------|---|--------------|------|------------|------------------------|--|--|--|--|
| PARAMETER                                      | SYMBOL                            | TEST CONDITIONS                             | MIN.         | TYP. | MAX.       | UNITS                  |  |  |  |  |
| Maximum junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |   | -65          | -    | 175        | °C                     |  |  |  |  |
| Thermal resistance, junction to case           | R <sub>thJC</sub>                 |   | -            | -    | 3.0        |                        |  |  |  |  |
| Thermal resistance, junction to ambient        | R <sub>thJA</sub>                 |   | -            | -    | 50         | °C/W                   |  |  |  |  |
| Thermal resistance, case to heatsink           | R <sub>thCS</sub>                 | Mounting surface, flat, smooth, and greased | -            | 0.5  | -          |                        |  |  |  |  |
| Weight   |                                   |   | -            | 2.0  | -          | g                      |  |  |  |  |
| weight   |                                   |   | -            | 0.07 | -          | OZ.                    |  |  |  |  |
| Mounting torque                                |                                   |   | 6.0<br>(5.0) | -    | 12<br>(10) | kgf · cm<br>(lbf · in) |  |  |  |  |
| Marking device                                 |                                   | Case style TO-220AC 2L                      | MUR820       |      |            |                        |  |  |  |  |

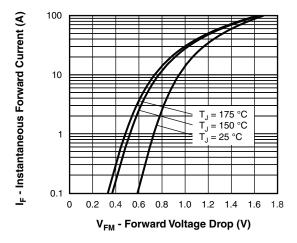


Fig. 1 - Maximum Forward Voltage Drop Characteristics

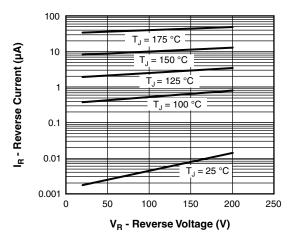


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

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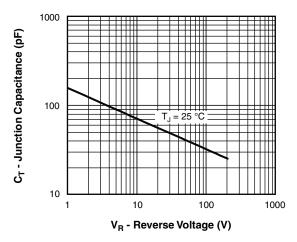


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

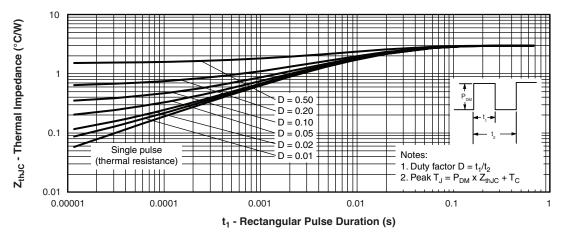


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

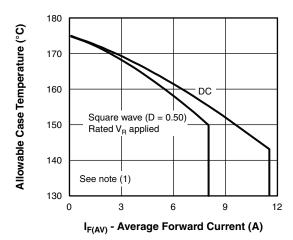


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

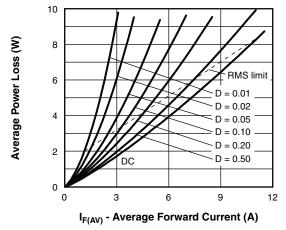


Fig. 6 - Forward Power Loss Characteristics

#### Note

<sup>&</sup>lt;sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$  (see fig. 6);  $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = rated V_R$ 

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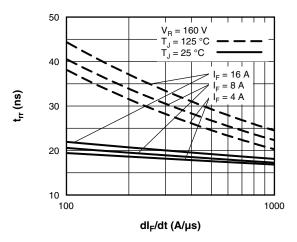


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

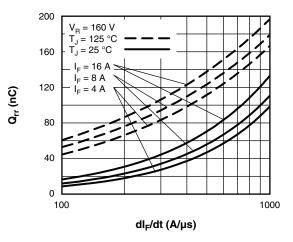
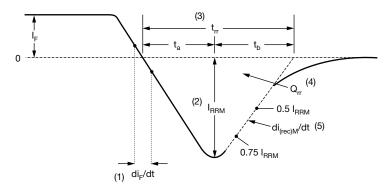


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{F}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

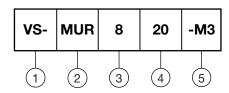
Fig. 9 - Reverse Recovery Waveform and Definitions



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### **ORDERING INFORMATION TABLE**

Device code



- Vishay Semiconductors product
- 2 Ultrafast MUR series
- Current rating (8 = 8 A)
- 4 Voltage rating (20 = 200 V)
- Environmental digit:
   -M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

| ORDERING INFORMATION (Example) |               |                         |  |  |  |  |  |  |  |  |
|--------------------------------|---------------|-------------------------|--|--|--|--|--|--|--|--|
| PREFERRED P/N                  | BASE QUANTITY | PACKAGING DESCRIPTION   |  |  |  |  |  |  |  |  |
| VS-MUR820-M3                   | 50            | Antistatic plastic tube |  |  |  |  |  |  |  |  |

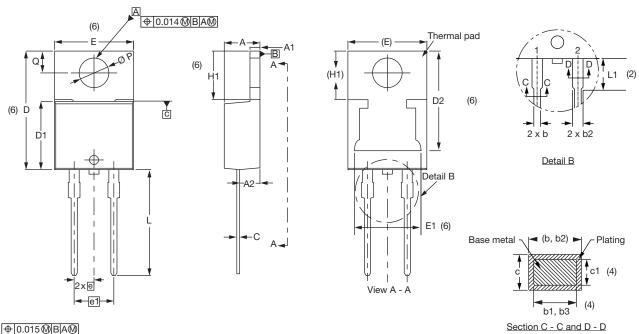
| LINKS TO RELATED DOCUMENTS                 |                          |  |  |  |  |  |  |  |
|--|--------------------------|--|--|--|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?96156</u> |                          |  |  |  |  |  |  |  |
| Part marking information                   | www.vishay.com/doc?95391 |  |  |  |  |  |  |  |

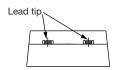


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## 2L TO-220AC

#### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AC

| SYMBOL  | MILLIM | IETERS | INC   | HES   | NOTES | NOTES |        | MILLIN | IETERS | INC   | HES   | NOTES |
|---------|--------|--------|-------|-------|-------|-------|--------|--------|--------|-------|-------|-------|
| STWIBOL | MIN.   | MAX.   | MIN.  | MAX.  | NOTES | NOTES | SYMBOL | MIN.   | MAX.   | MIN.  | MAX.  | NOTES |
| Α       | 4.25   | 4.65   | 0.167 | 0.183 |       |       | D2     | 11.68  | 13.30  | 0.460 | 0.524 | 6, 7  |
| A1      | 1.14   | 1.40   | 0.045 | 0.055 |       |       | E      | 10.11  | 10.51  | 0.398 | 0.414 | 3, 6  |
| A2      | 2.50   | 2.92   | 0.098 | 0.115 |       |       | E1     | 6.86   | 8.89   | 0.270 | 0.350 | 6     |
| b       | 0.69   | 1.01   | 0.027 | 0.040 |       |       | е      | 2.41   | 2.67   | 0.095 | 0.105 |       |
| b1      | 0.38   | 0.97   | 0.015 | 0.038 | 4     |       | e1     | 4.88   | 5.28   | 0.192 | 0.208 |       |
| b2      | 1.20   | 1.73   | 0.047 | 0.068 |       |       | H1     | 6.09   | 6.48   | 0.240 | 0.255 | 6     |
| b3      | 1.14   | 1.73   | 0.045 | 0.068 | 4     |       | L      | 13.52  | 14.02  | 0.532 | 0.552 |       |
| С       | 0.36   | 0.61   | 0.014 | 0.024 |       |       | L1     | 3.32   | 3.82   | 0.131 | 0.150 | 2     |
| c1      | 0.36   | 0.56   | 0.014 | 0.022 | 4     |       | ØΡ     | 3.54   | 3.91   | 0.139 | 0.154 |       |
| D       | 14.85  | 15.35  | 0.585 | 0.604 | 3     |       | Q      | 2.60   | 3.00   | 0.102 | 0.118 |       |
| D1      | 8.38   | 9.02   | 0.330 | 0.355 |       |       |        | •      | •      |       |       |       |

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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